In the Claims

Claims 1-31 [canceled].

32. [Currently Amended] A temperature sensing apparatus fabrication method ~~of sensing temperature of an electronic device workpiece~~ comprising:

~~providing an electronic device workpiece;~~

forming a cavity in an electronic device workpiece;

providing a temperature sensing device within the cavity and in a configuration to sense temperature of the electronic device workpiece;

supporting [[a]] the temperature sensing device using the electronic device workpiece;

providing an electrical interconnect upon a surface of the electronic device workpiece; and

electrically coupling the electrical interconnect with the temperature sensing device~~; and~~

~~sensing temperature of the electronic device workpiece using the temperature sensing device~~.

33. [Currently Amended] The method according to claim 32 ~~further comprising~~ wherein the electrically coupling comprises wire bonding the electrical interconnect and the temperature sensing device.

34. [Cancelled].

35. [Currently Amended] The method according to claim [[34]] 32 wherein the forming the cavity comprises anisotropically etching the electronic device workpiece.

36. [Currently Amended] The method according to claim [[34]] 32 wherein the forming the cavity comprises isotropically etching the electronic device workpiece.

37. [Original] The method according to claim 32 further comprising forming the temperature sensing device.

38. [Original] The method according to claim 37 wherein the forming the temperature sensing device comprises forming a resistance temperature device.

39. [Original] The method according to claim 32 further comprising electrically coupling the electrical interconnect with external circuitry.

40. [Original] The method according to claim 32 further comprising electrically coupling the temperature sensing device with an edge of the electronic device workpiece using the electrical interconnect.

41. [Original] The method according to claim 32 wherein the providing the electrical interconnect comprises forming a conductive trace.

42. [Original] The method according to claim 32 further comprising contacting the electrical interconnect with the temperature sensing device.

43. [Previously Presented] The method according to claim 32 wherein the sensing comprises sensing temperature of the electronic device workpiece comprising a semiconductive wafer.

Claims 44-52 [canceled].

53. [Currently Amended] A temperature sensing apparatus fabrication method ~~of sensing temperature of an electronic device workpiece~~ comprising:

providing an electronic device workpiece;

forming a plurality of temperature sensing ~~device~~ devices over the electronic device workpiece, ~~the forming including providing~~ the temperature sensing ~~device~~ devices being configured to sense temperature in three dimensions of ~~in a temperature sensing relation with~~ the electronic device workpiece~~; and~~

~~sensing the temperature of the electronic device workpiece using the temperature sensing device~~.

54. [Currently Amended] The method according to claim 53 further comprising:

providing an electrical interconnect upon the electronic device workpiece; and

electrically coupling the electrical interconnect with at least one of the temperature sensing ~~device~~ devices.

55. [Original] The method according to claim 54 wherein the providing the electrical interconnect comprises forming a conductive trace.

56. [Currently Amended] The method according to claim 54 wherein the electrically coupling comprises wire bonding the electrical interconnect and the at least one of the temperature sensing ~~device~~ devices.

57. [Currently Amended] The method according to claim 54 wherein the electrically coupling includes contacting the electrical interconnect and the at least one of the temperature sensing ~~device~~ devices.

58. [Currently Amended] The method according to claim 53 further comprising:

forming a cavity in the electronic device workpiece; and

providing at least one of the temperature sensing ~~device~~ devices within the cavity.

59. [Original] The method according to claim 58 wherein the forming the cavity comprises anisotropically etching the electronic device workpiece.

60. [Currently Amended] The method according to claim 53 wherein the forming comprises forming the temperature sensing devices individually comprising a resistance temperature device.

61. [Cancelled].

62. [Currently Amended] A temperature sensing apparatus fabrication method ~~of sensing temperature of an electronic device workpiece~~ comprising:

~~providing an electronic device workpiece;~~

supporting a temperature sensing device using ~~the~~ an electronic device workpiece;

providing the temperature sensing device in a temperature sensing ~~relation~~ relationship with the electronic device workpiece;

providing an electrical interconnect upon a surface of the electronic device workpiece; and

electrically coupling the electrical interconnect with the temperature sensing device comprising wire bonding the electrical interconnect and the temperature sensing device.

63. [Cancelled].

64. [Cancelled].

65. [Original] The method according to claim 62 further comprising:

forming a cavity in the electronic device workpiece; and

providing the temperature sensing device within the cavity.

66. [Original] The method according to claim 65 wherein the forming the cavity comprises anisotropically etching the electronic device workpiece.

67. [Previously Presented] The method according to claim 62 further comprising forming the temperature sensing device upon the electronic device workpiece.

68. [Original] The method according to claim 62 further comprising electrically coupling the electrical interconnect with circuitry external to the electronic device workpiece.

69. [Original] The method according to claim 62 further comprising electrically coupling the temperature sensing device with an edge of the electronic device workpiece using the electrical interconnect.

70. [Original] The method according to claim 62 wherein the providing the electrical interconnect comprises forming a conductive trace.

71. [Currently Amended] A temperature sensing method comprising:

supporting a plurality of temperature sensing ~~device~~ devices using a wafer, and wherein the temperature sensing devices are individually in a temperature sensing relationship with respect to the wafer;

~~providing the temperature sensing device in a temperature sensing relationship with respect to the wafer;~~

exposing the wafer and the temperature sensing ~~device~~ devices to process conditions effective to form at least one electronic device; and

sensing [[a]] temperature of the wafer in three dimensions of the wafer using the temperature sensing ~~device~~ devices during the exposing.

72. [Previously Presented] The method of claim 71 further comprising adjusting the process conditions responsive to the sensing.

73. [Previously Presented] The method of claim 71 further comprising sensing the temperature of the wafer at a plurality of positions covering substantially an entirety of a surface of the wafer.

74. [Cancelled].

75. [Currently Amended] The method of claim 71 wherein the wafer comprises a production wafer, and further comprising forming the at least one electronic device using the wafer ~~responsive to~~ during the exposing.

76. [Currently Amended] The method according to claim 32 wherein the ~~providing~~ the electronic device workpiece comprises ~~providing a wafer comprising silicon~~ a silicon wafer.

77. [Currently Amended] The method according to claim 32 ~~wherein the sensing comprises sensing~~ further comprising configuring the temperature sensing device to sense the temperature of the electronic device workpiece during fabrication of an electronic device using the electronic device workpiece.

78. [Previously Presented] The method according to claim 53 wherein the providing the electronic device workpiece comprises providing a wafer comprising silicon.

79. [Currently Amended] The method according to claim 53 wherein the ~~sensing comprises sensing~~ wherein the temperature sensing devices are individually configured to

sense the temperature of the electronic device workpiece during fabrication of an electronic device using the electronic device workpiece.

80. [Currently Amended] The method according to claim 62 wherein ~~the providing~~ the electronic device workpiece comprises ~~providing a wafer comprising silicon~~ a silicon wafer

81. [Currently Amended] The method according to claim 62 ~~further comprising sensing~~ wherein the temperature sensing device is configured to sense temperature of the electronic device workpiece during fabrication of an electronic device using the electronic device workpiece.

82. [Currently Amended] The method of claim 71 wherein the supporting comprises supporting the temperature sensing ~~device~~ devices using the wafer comprising silicon.

83. [Previously Presented] The method of claim 71 wherein the sensing the temperature comprises sensing the temperature of the wafer during fabrication of an electronic device using the wafer.

84. [New] A temperature sensing apparatus fabrication method comprising:

providing an electronic device workpiece;

forming a temperature sensing device over the electronic device workpiece, the forming including providing the temperature sensing device in a temperature sensing relation with the electronic device workpiece;

providing an electrical interconnect upon the electronic device workpiece;

electrically coupling the electrical interconnect with the temperature sensing device; and

wherein the electrically coupling comprises wire bonding the electrical interconnect and the temperature sensing device.

85. [New] A temperature sensing apparatus fabrication method comprising:

providing an electronic device workpiece;

forming a cavity in the electronic device workpiece; and

forming a temperature sensing device within the cavity, the temperature sensing device being configured to sense temperature of the electronic device workpiece.

86. [New] The method according to claim 85 wherein the forming the cavity comprises anisotropically etching the electronic device workpiece.

87. [New] A temperature sensing apparatus fabrication method comprising:

forming a cavity in an electronic device workpiece;

supporting a temperature sensing device using the electronic device workpiece, the supporting comprising providing the temperature sensing device within the cavity in a temperature sensing relationship with the electronic device workpiece;

providing an electrical interconnect upon a surface of the electronic device workpiece; and

electrically coupling the electrical interconnect with the temperature sensing device.

88. [New] The method according to claim 87 wherein the forming the cavity comprises anisotropically etching the electronic device workpiece.

89. [New] A temperature sensing method comprising:

supporting a temperature sensing device using a wafer;

exposing the wafer and the temperature sensing device to process conditions effective to form at least one electronic device;

sensing a temperature of the wafer using the temperature sensing device during the exposing; and

during the exposing, forming the at least one electronic device using the wafer.